

ST Wafer

High Strength Si wafers

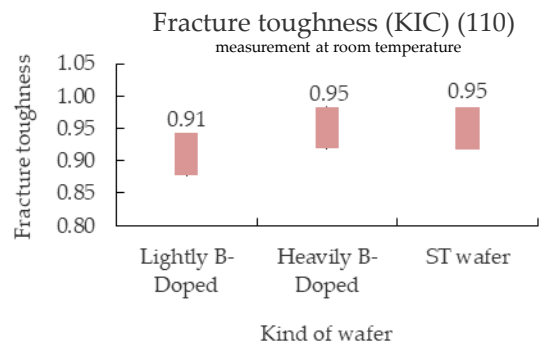
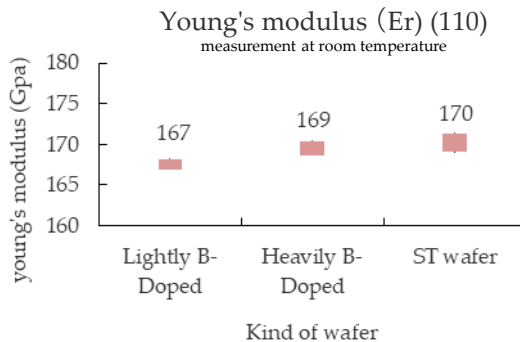
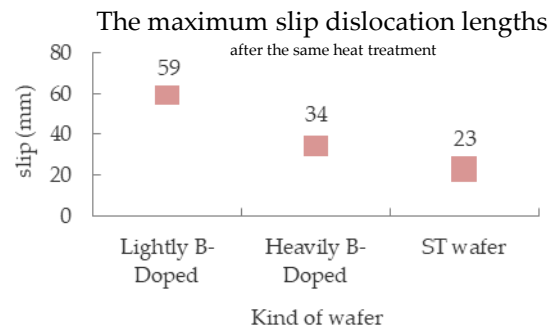
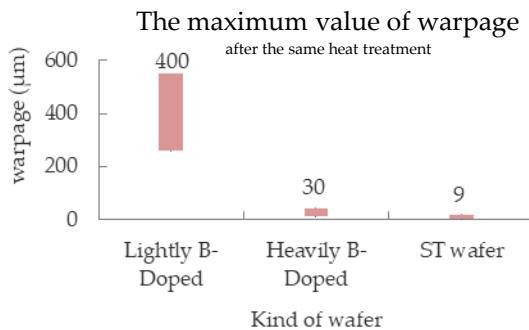
Features

- Improved mechanical strength by optimization of impurity.
- Exhibit heat resistance with stress free performance.
- Reduce slips and warpage for thermal and hetero-epitaxial process.

Application

- **Substrate for GaN (Gallium Nitride) epitaxial growth.**
- MEMS for requiring high strength.
- p/p+ epitaxial wafers for thermal shock resistance.

Advantage



Specification

- Orientation: $\langle 111 \rangle$, $\langle 100 \rangle$, $\langle 110 \rangle$
- Diameter : 4, 5, 6 inch
- Dopant : B (P type)
- Resistivity : $\leq 0.02 \text{ Ohm-cm}$
- Thickness : $\leq 1,000 \text{ um}$ (Customizable)



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